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**(54) SELF-ALIGNED CONTACT AND MANUFACTURE
THEREOF**

be prevented.

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(57) Abstract:

PROBLEM TO BE SOLVED: To prevent a short failure caused by misalignment, by a method wherein self-aligned contact pads are formed in layers so as to be self-aligned with gate electrodes and bit lines.

SOLUTION: Insulating-films 108 are formed on insulating films 104 including self-aligned contact pads E6 formed on a semiconductor substrate 100, and a material layer 114 in a certain etching selective ratio to the insulating film 108 is formed on the insulating film 108 so as to surround bit lines 112. Self-aligned contact pads 118 electrically connected to the self-aligned contact pads 106 are formed on each side of the bit lines 112. The self-aligned contact pads 106 and 118 are formed in two layers, whereby the contact pads are self-aligned with gate electrodes and the bit lines 112, and a short failure caused by misalignment can

